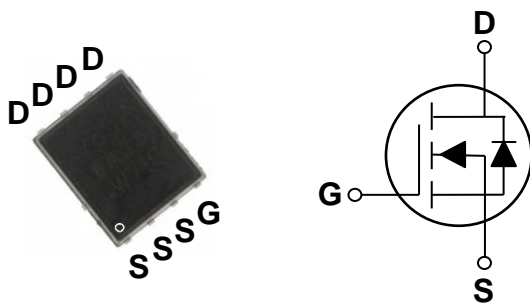


## General Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

## PPAK5X6 Pin Configuration



BVDSS	RDSON	ID
100V	17mΩ	54A

## Features

- 100V,54A,  $R_{DS(ON)} = 17m\Omega @ V_{GS} = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

## Applications

- Networking
- Load Switch
- LED applications



## Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous ( $T_C=25^\circ\text{C}$ )	54	A
	Drain Current – Continuous ( $T_C=100^\circ\text{C}$ )	34	A
$I_{DM}$	Drain Current – Pulsed <sup>1</sup>	216	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	101	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	45	A
$P_D$	Power Dissipation ( $T_C=25^\circ\text{C}$ )	136	W
	Power Dissipation – Derate above $25^\circ\text{C}$	1.09	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-50 to 150	$^\circ\text{C}$

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.92	$^\circ\text{C}/\text{W}$

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	---	0.09	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	---	14.3	17	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	15.8	20	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.0	1.6	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-4.54	---	mV/°C
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	---	10	---	S

**Dynamic and switching Characteristics**

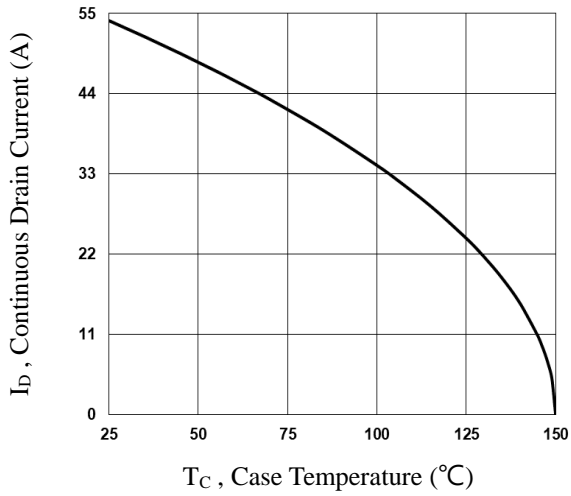
Q <sub>g</sub>	Total Gate Charge <sup>3, 4</sup>	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =5A	---	66.7	100	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3, 4</sup>		---	13.4	26	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3, 4</sup>		---	14.6	28	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3, 4</sup>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A	---	23	46	ns
T <sub>r</sub>	Rise Time <sup>3, 4</sup>		---	11	22	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3, 4</sup>		---	57	114	
T <sub>f</sub>	Fall Time <sup>3, 4</sup>		---	26	58	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, F=1MHz	---	4812	7200	pF
C <sub>oss</sub>	Output Capacitance		---	220	330	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	107	160	
R <sub>g</sub>	Gate resistance		V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	1.6	

**Drain-Source Diode Characteristics and Maximum Ratings**

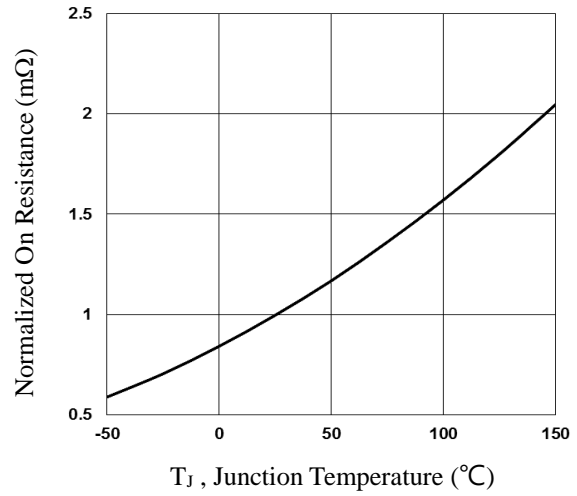
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	54	A
I <sub>SM</sub>	Pulsed Source Current		---	---	108	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

Note :

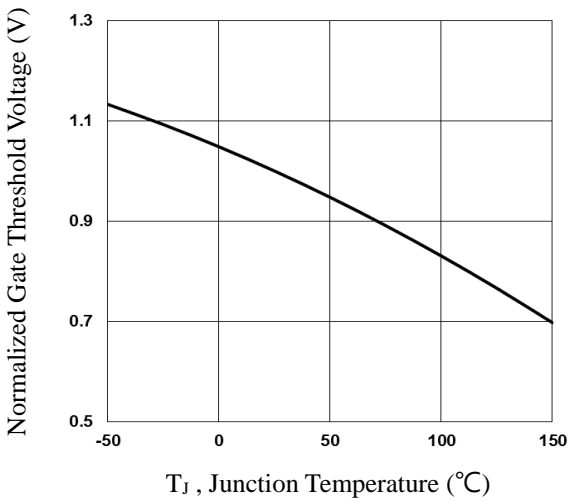
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=45A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



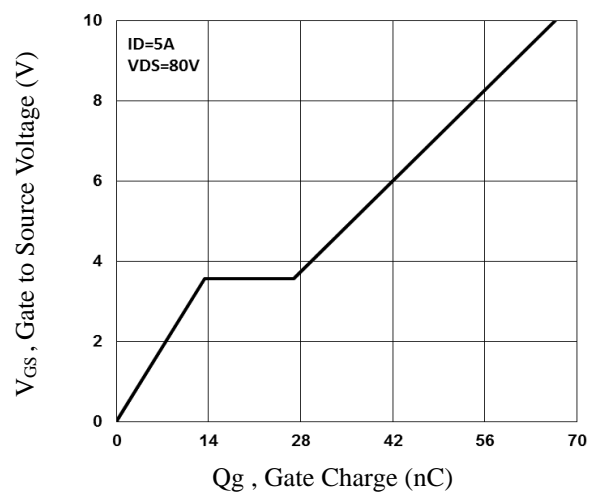
**Fig.1 Continuous Drain Current vs. TC**



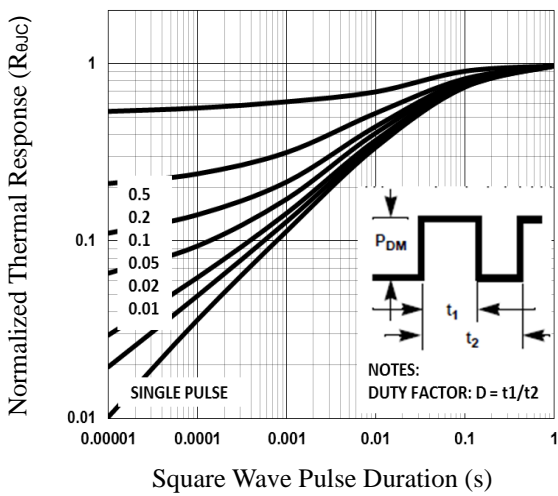
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$**



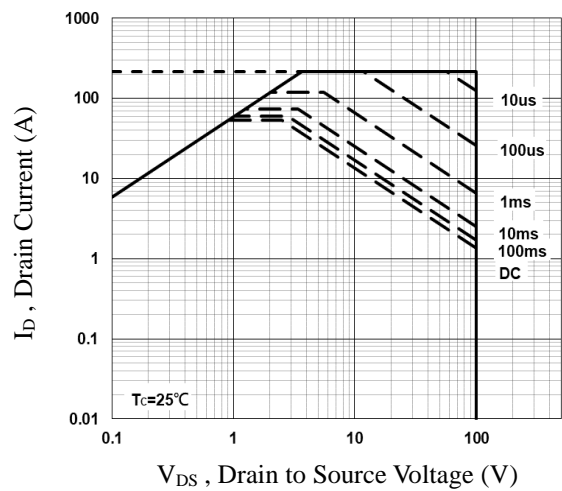
**Fig.3 Normalized  $V_{th}$  vs.  $T_J$**



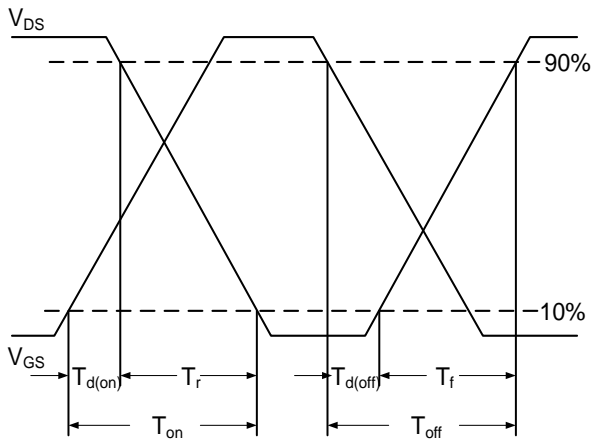
**Fig.4 Gate Charge Characteristics**



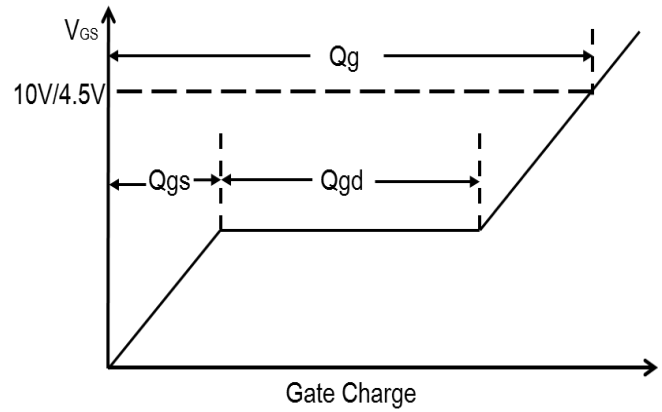
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

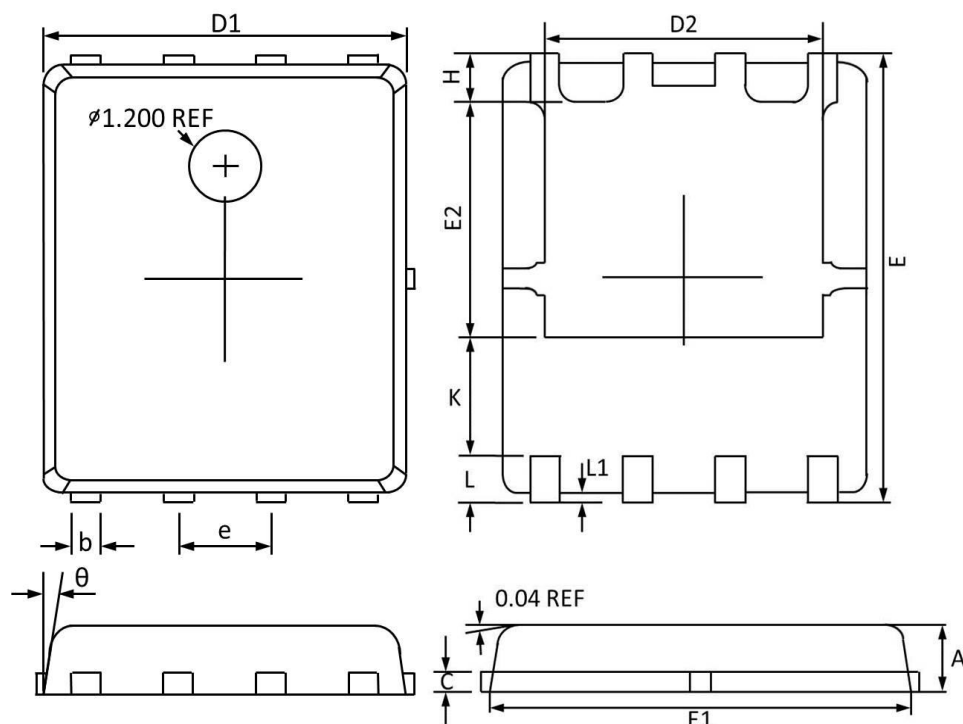


**Fig.7 Switching Time Waveform**



**Fig.8 Gate Charge Waveform**

**PPAK5X6 PACKAGE INFORMATION**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.100	0.800	0.043	0.031
b	0.510	0.330	0.020	0.013
C	0.300	0.200	0.012	0.008
D1	5.100	4.800	0.201	0.189
D2	4.100	3.610	0.161	0.142
E	6.200	5.900	0.244	0.232
E1	5.900	5.700	0.232	0.224
E2	3.780	3.350	0.149	0.132
e	1.27BSC		0.05BSC	
H	0.700	0.410	0.028	0.016
K	1.500	1.100	0.059	0.043
L	0.710	0.510	0.028	0.020
L1	0.200	0.060	0.008	0.002
$\theta$	12°	0°	12°	0°